

# MBR10H100CT - MBR10H200CT

10.0 AMPS. Schottky Barrier Rectifiers

**TO-220AB** 



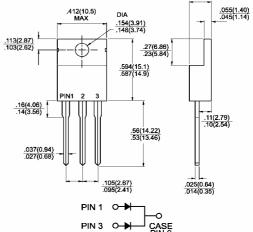
## **Features**

- Plastic material used carries Underwriters Laboratory Classifications 94V-0
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- For use in power supply output rectification, power management, instrumentation
- Guardring for overvoltage protection
- High temperature soldering guaranteed: 260°C/10 seconds,0.25"(6.35mm)from case

## **Mechanical Data**

- Cases: JEDEC TO-220AB molded plastic body
- Terminals: Pure tin plated, lead free. solderable per MIL-STD-750, Method 2026
- Polarity: As marked
- Mounting position: Any
- Mounting torque: 5 in. Ibs. max Weight: 0.08 ounce, 2.24 grams

## .412(10.5) MAX DIA .154(3.91) .148(3.74) .055(1.40) .27(6.86) .594(15.1) .587(14.9)



Dimensions in inches and (millimeters)

# **Maximum Ratings and Electrical Characteristics**

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	MBR 10H100CT	MBR 10H150CT	MBR 10H200CT	Units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	100	150	200	V
Maximum RMS Voltage	$V_{RMS}$	70	105	140	V
Maximum DC Blocking Voltage	$V_{DC}$	100	150	200	V
Maximum Average Forward Rectified Current at Tc=125°C	I <sub>(AV)</sub>	10			Α
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20KHz) at Tc=125°C	I <sub>FRM</sub>	32			Α
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I <sub>FSM</sub>	120			Α
Peak Repetitive Reverse Surge Current (Note 1)	I <sub>RRM</sub>	1.0 0.5		Α	
$\begin{array}{lll} \text{Maximum Instantaneous Forward Voltage at:} \\ \text{(Note 2)} & I_F = 5\text{A, } T_\text{C} = 25^{\circ}\text{C} \\ & I_F = 5\text{A, } T_\text{C} = 125^{\circ}\text{C} \\ & I_F = 10\text{A, } T_\text{C} = 25^{\circ}\text{C} \\ & I_F = 10\text{A, } T_\text{C} = 125^{\circ}\text{C} \\ \end{array}$	V <sub>F</sub>	0.85 0.75 0.95 0.85	0.88 0.75 0.97 0.85		V
Maximum Instantaneous Reverse Current  @ Tc =25 °C at Rated DC Blocking Voltage  @ Tc=125 °C (Note 2)	I <sub>R</sub>	5 1.0			uA mA
Voltage Rate of Change (Rated V <sub>R</sub> )	dV/dt	10,000			V/uS
Maximum Typical Thermal Resistance (Note 3)	R <sub>0</sub> JC	1.5			°C/W
Operating Junction Temperature Range	TJ	-65 to +175			°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +175			°C

Notes:

- 1. 2.0us Pulse Width, f=1.0 KHz
- 2. Pulse Test: 300us Pulse Width, 1% Duty Cycle
- 3. Thermal Resistance from Junction to Case Per Leg, Mount on Heatsink Size of 2 in x 3 in x 0.25in Al-Plate.

Version: A07



### RATINGS AND CHARACTERISTIC CURVES (MBR10H100CT THRU MBR10H200CT)

